



ISO100

Optically-Coupled Linear ISOLATION AMPLIFIER

FEATURES

- EASY TO USE, SIMILAR TO AN OP AMP
 $V_{OUT}/I_{IN} = R_F$, Current Input
 $V_{OUT}/V_{IN} = R_F/R_{IN}$, Voltage Input
- 100% TESTED FOR BREAKDOWN:
 750V Continuous Isolation Voltage
- ULTRA-LOW LEAKAGE: 0.3 μ A, max, at 240V/60Hz
- WIDE BANDWIDTH: 60kHz
- 18-PIN DIP PACKAGE

APPLICATIONS

- INDUSTRIAL PROCESS CONTROL
 Transducer Sensing
 (Thermocouples, RTD, Pressure Bridges)
 4mA to 20mA Loops
 Motor and SCR Control
 Ground Loop Elimination
- BIOMEDICAL MEASUREMENTS
- TEST EQUIPMENT
- DATA ACQUISITION

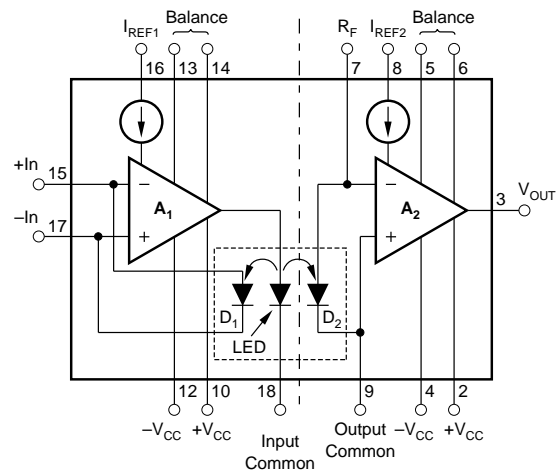
DESCRIPTION

The ISO100 is an optically-coupled isolation amplifier. High accuracy, linearity, and time-temperature stability are achieved by coupling light from an LED back to the input (negative feedback) as well as forward to the output. Optical components are carefully matched and the amplifier is actively laser-trimmed to assure excellent tracking and low offset errors.

The circuit acts as a current-to-voltage converter with a minimum of 750V (2500V test) between input and output terminals. It also effectively breaks the galvanic connection between input and output commons as indicated by the ultra-low 60Hz leakage current of 0.3 μ A at 250V. Voltage input operation is easily achieved by using one external resistor.

Versatility along with outstanding DC and AC performance provide excellent solutions to a variety of challenging isolation problems. For example, the ISO100 is capable of operating in many modes, including: noninverting (unipolar and bipolar) and inverting (unipolar and bipolar) configurations. Two precision current sources are provided to accomplish bipolar operation. Since these are not required for unipolar operation, they are available for external use (see Applications section).

Designs using the ISO100 are easily accomplished with relatively few external components. Since V_{OUT} of the ISO100 is simply $I_{IN}R_F$, gains can be changed by altering one resistor value. In addition, the ISO100 has sufficient bandwidth (DC to 60kHz) to amplify most industrial and test equipment signals.



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SPECIFICATIONS

ELECTRICAL

At $T_A = +25^\circ\text{C}$ and $\pm V_{CC} = 15\text{VDC}$, unless otherwise specified.

PARAMETER	CONDITIONS	ISO100AP			ISO100BP			ISO100CP			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
ISOLATION											
Voltage											V
Rated Continuous, AC peak or DC ⁽¹⁾	10s	750			*			*			V
Test Breakdown, DC		2500			*			*			V
Rejection ⁽²⁾ DC			5			*		*	*		pA/V
AC	$R_{IN} = 10\text{k}\Omega$, Gain = 100		146			*		*	*		dB
	60Hz, 480V, $R_F = 1\text{M}\Omega$		400			*		*	*		pA/V
	$R_{IN} = 10\text{k}\Omega$, Gain = 100		108			*		*	*		dB
Impedance			$10^{12} 2.5$			*		*	*		ΩpF
Leakage Current	240Vrms, 60Hz			0.3			*			*	μA , rms
OFFSET VOLTAGE (RTI)											
Input Stage (V_{OSI})											μV
Initial Offset				500			300			200	$\mu\text{V}/^\circ\text{C}$
vs Temperature				5			2			2	$\mu\text{V}/^\circ\text{C}$
vs Input Power Supplies				105			*			*	dB
vs Time			1			*		*		*	$\mu\text{V}/\text{kHr}$
Output Stage (V_{OSO})											μV
Initial Offset				500			300			200	$\mu\text{V}/^\circ\text{C}$
vs Temperature				5			2			2	$\mu\text{V}/^\circ\text{C}$
vs Output Power Supplies				105			*			*	dB
vs Time			1			*		*		*	$\mu\text{V}/\text{kHr}$
Common-Mode Rejection Ratio ⁽²⁾	60Hz, $R_F = 1\text{M}\Omega$			3		*	*	*	*	*	nA/V
	$R_{IN} = 10\text{k}\Omega$, Gain = 100			90		*	*	*	*	*	dB
Common-Mode Range		± 10			*			*			V
REFERENCE CURRENT SOURCES											
Magnitude											μA
Nominal		10.5	12	12.5	*	*	*	*	*	*	μA
vs Temperature				300		*	*	*	*	*	ppm/ $^\circ\text{C}$
vs Power Supplies			0.3	3		*	*	*	*	*	nA/V
Matching											nA
Nominal			50			*	*	*	*	*	ppm/ $^\circ\text{C}$
vs Temperature			150			*	*	*	*	*	nA/V
vs Power Supplies			0.3			*	*	*	*	*	V
Compliance Voltage		-10		+15	*	*	*	*	*	*	V
Output Resistance			2×10^9			*	*	*	*	*	Ω
FREQUENCY RESPONSE											
Small Signal Bandwidth	Gain = $1\text{V}/\mu\text{A}$		60			*	*	*	*	*	kHz
Full Power Bandwidth	Gain = $1\text{V}/\mu\text{A}$, $V_O = \pm 10\text{V}$		5			*	*	*	*	*	kHz
Slew Rate		0.22	0.31		*	*	*	*	*	*	V/ μs
Settling Time	0.1%		100			*	*	*	*	*	μs
TEMPERATURE RANGE											
Specification		-25		+85	*		*	*	*	*	$^\circ\text{C}$
Operating		-40		+100	*		*	*	*	*	$^\circ\text{C}$
Storage		-40		+100	*		*	*	*	*	$^\circ\text{C}$
UNIPOLAR OPERATION											
GENERAL PARAMETERS											
Input Current Range											μA
Linear Operation		-20		-0.02	*		*	*	*	*	μA
Without Damage		-1		+1	*		*	*	*	*	mA
Input Impedance			0.1			*		*	*	*	Ω
Output Voltage Swing	$R_L = 2\text{k}\Omega$, $R_F = 1\text{M}\Omega$	-10		0	*		*	*	*	*	V
Output Impedance	DC, Open-Loop		1200			*		*	*	*	Ω
GAIN											
Initial Error (adjustable to zero)	$V_O = R_F (I_{IN})$		2	5		1	2		1	2	% of FS
vs Temperature			0.03	0.07		0.01	0.05		0.005	0.03	%/ $^\circ\text{C}$
vs Time			0.05			*			*		%/kHr
Nonlinearity ⁽³⁾			0.1	0.4		0.03	0.1		0.02	0.07	%
CURRENT NOISE											
0.01Hz to 10Hz	$I_{IN} = 0.2\mu\text{A}$		20			*			*		pAp-p
10Hz			1			*			*		$\text{pA}/\sqrt{\text{Hz}}$
100Hz			0.7			*			*		$\text{pA}/\sqrt{\text{Hz}}$
1kHz			0.65			*			*		$\text{pA}/\sqrt{\text{Hz}}$



SPECIFICATIONS (CONT)

ELECTRICAL

At $T_A = +25^\circ\text{C}$ and $\pm V_{CC} = 15\text{VDC}$, unless otherwise specified.

PARAMETER	CONDITIONS	ISO100AP			ISO100BP			ISO100CP			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
INPUT OFFSET CURRENT (I_{OS}) Initial Offset vs Temperature vs Power Supplies vs Time			1 0.05 0.1 100	10		*	*		*	*	nA nA/ $^\circ\text{C}$ nA/V pA/kHr
POWER SUPPLIES Input Stage Voltage (rated performance) Voltage (derated performance) Supply Current Output Stage Voltage (rated performance) Voltage (derated performance) Supply Current Short Circuit Current Limit	$I_{IN} = -0.02\mu\text{A}$ $I_{IN} = -20\mu\text{A}$ $V_O = 0$	± 7 ± 7	± 15 ± 1.1 $+8, -1.1$ ± 15 ± 1.1	± 18 ± 2 $+13, -2$ ± 18 ± 2 ± 40	*	*	*	*	*	*	V V mA mA V V mA mA
BIPOLAR OPERATION											
GENERAL PARAMETERS Input Current Range Linear Operation Without Damage Input Impedance Output Voltage Swing Output Impedance	$R_L = 2\text{k}\Omega$, $R_F = 1\text{M}\Omega$	-10 -1	0.1	+10 +1	*	*	*	*	*	*	μA mA Ω V Ω
GAIN Initial Error (Adjustable To Zero) vs Temperature vs Time Nonlinearity ⁽³⁾	$V_O = R_F (I_{IN})$		2 0.03 0.05 0.1	5 0.07 0.4		1 0.01 *	2 0.05 0.1		1 0.005 *	2 0.03 0.07	% of FS %/ $^\circ\text{C}$ %/kHr %
CURRENT NOISE 0.01Hz to 10Hz 10Hz 100Hz 1kHz	$I_{IN} = 0.2\mu\text{A}$		1.5 17 7 6			*	*		*	*	nA, p-p pA/ $\sqrt{\text{Hz}}$ pA/ $\sqrt{\text{Hz}}$ pA/ $\sqrt{\text{Hz}}$
INPUT OFFSET CURRENT (I_{OS}, bipolar⁽⁴⁾) Initial Offset vs Temperature vs Power Supplies vs Time			40 3 250	200 0.7		20 *	70 *		10 *	35 1 *	nA nA/ $^\circ\text{C}$ nA/V pA/kHr
POWER SUPPLIES Input Stage Voltage (rated performance) Voltage (derated performance) Supply Current Output Stage Voltage (rated performance) Voltage (derated performance) Supply Current Short Circuit Current Limit	$I_{IN} = +10\mu\text{A}$ $I_{IN} = -10\mu\text{A}$ $V_O = 0$	± 7 ± 7	± 15 $+2, -1.1$ $+8, -1.1$ ± 15 ± 1.1	± 18 $+3, -2$ $+13, -2$ ± 18 ± 2 ± 40	*	*	*	*	*	*	V V mA mA V V mA mA

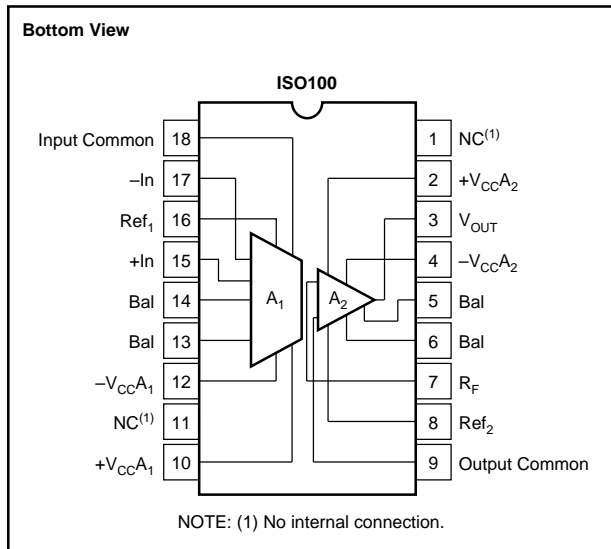
* Same as ISO100AP.

NOTES: (1) See Typical Performance Curves for temperature effects. (2) See Theory of Operation section for definitions. For dB see Ex. 2, CM and HV errors. (3) Nonlinearity is the peak deviation from a "best fit" straight line expressed as a percent of full scale output. (4) Bipolar offset current includes effects of reference current mismatch and unipolar offset current.

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PIN CONFIGURATION



ORDERING INFORMATION

PRODUCT	PACKAGE	TEMPERATURE RANGE
ISO100AP	18-Pin Bottom-Braze DIP	-25°C to +85°C
ISO100BP	18-Pin Bottom-Braze DIP	-25°C to +85°C
ISO100CP	18-Pin Bottom-Braze DIP	-25°C to +85°C

ABSOLUTE MAXIMUM RATINGS

Supply Voltages	±18V
Isolation Voltage, AC pk or DC	750V
Input Current	±1mA
Storage Temperature Range	-40°C to +100°C
Lead Temperature (soldering, 10s)	+300°C
Output Short-Circuit Duration	Continuous to Ground

PACKAGE INFORMATION

PRODUCT	PACKAGE	PACKAGE DRAWING NUMBER ⁽¹⁾
ISO100AP	18-Pin Bottom-Braze DIP	220
ISO100BP	18-Pin Bottom-Braze DIP	220
ISO100CP	18-Pin Bottom-Braze DIP	220

NOTE: (1) For detailed drawing and dimension table, please see end of data sheet, or Appendix C of Burr-Brown IC Data Book.



ELECTROSTATIC DISCHARGE SENSITIVITY

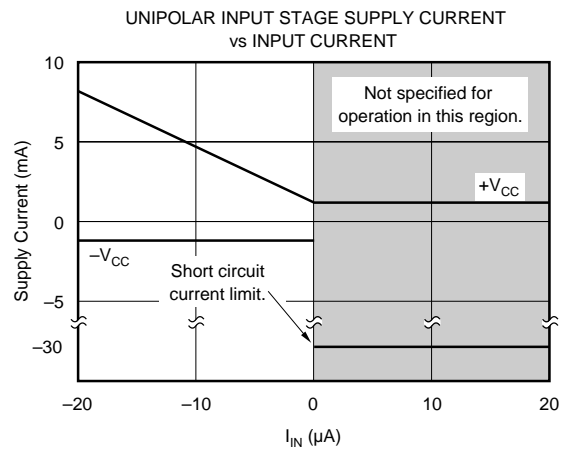
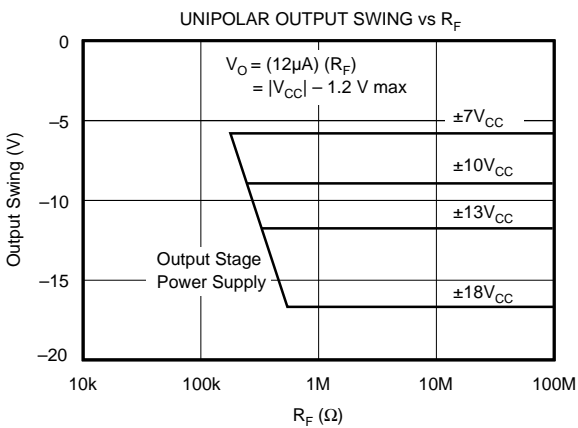
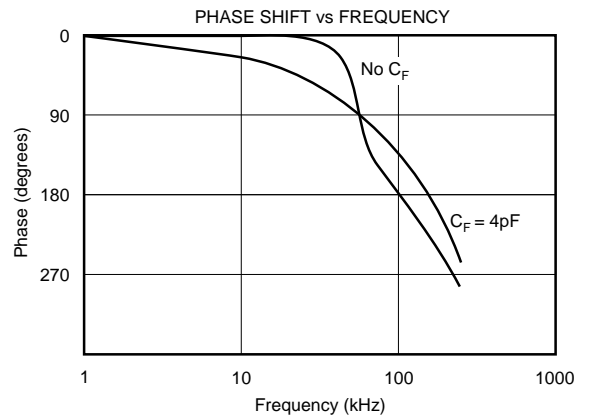
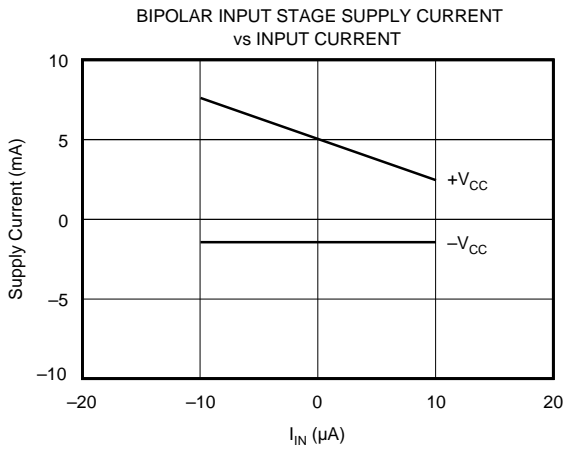
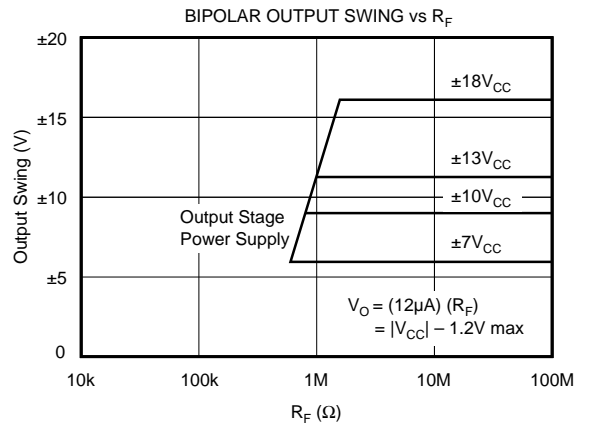
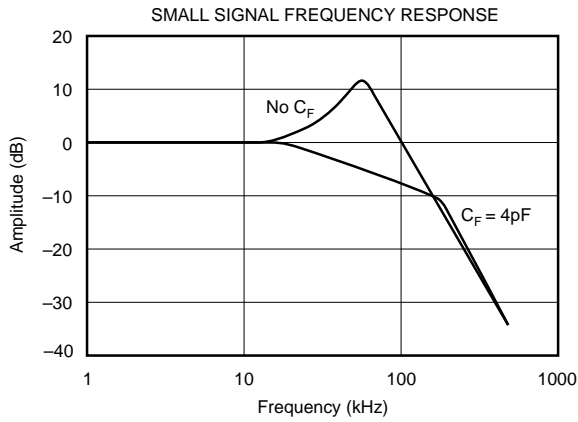
This integrated circuit can be damaged by ESD. Burr-Brown recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.



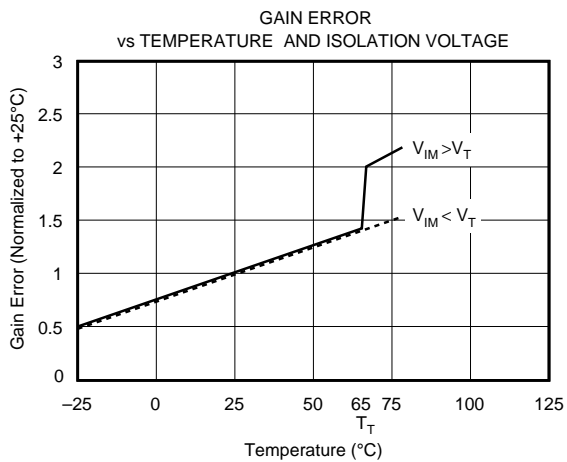
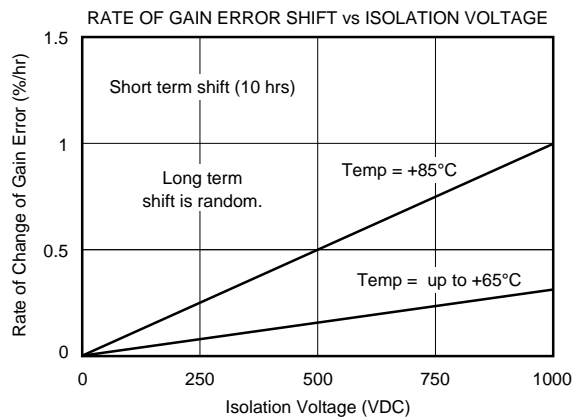
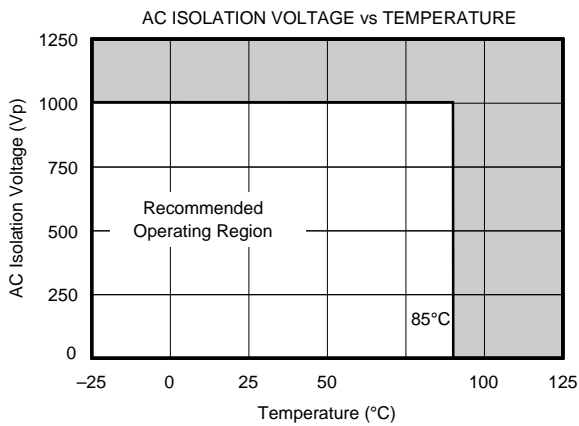
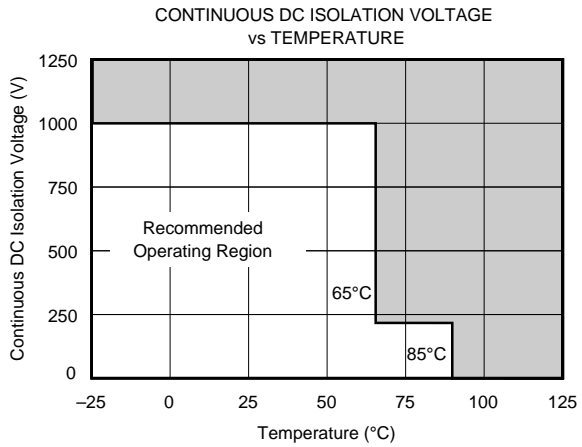
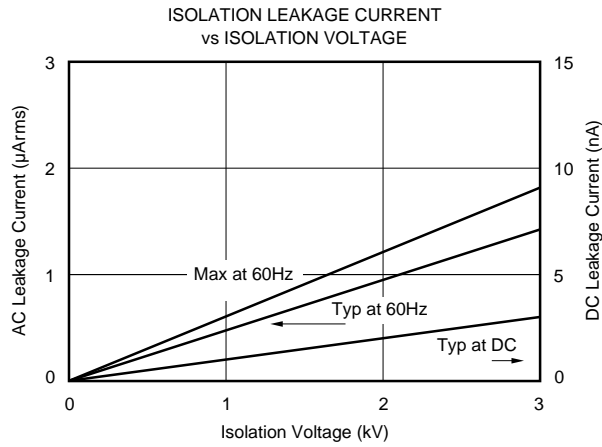
TYPICAL PERFORMANCE CURVES

At $T_A = +25^\circ\text{C}$, $\pm V_{CC} = 15\text{VDC}$, unless otherwise specified.



TYPICAL PERFORMANCE CURVES (CONT)

At $T_A = +25^\circ\text{C}$, $\pm V_{CC} = 15\text{VDC}$, unless otherwise specified.



NOTES: V_T and T_T approximate the threshold for the indicated gain shift. This is caused by the properties of the optical cavity.
 $T_T \approx +65^\circ\text{C}$, $V_T \approx 200\text{VDC}$. Shift does not occur for AC voltages.

V_{IM} = Isolation-Mode Voltage
 V_T = Threshold Voltage
 T_T = Threshold Temperature

Assuming $I_{IN} = 0$, the photodiode has to supply all the I_{REF1} current. Again, due to symmetry, $I_{D1} = I_{D2}$. Since the two references are matched, the current generated by D_2 will equal I_{REF2} . This results in no current flow in R_F , and the output voltage will be zero. When I_{IN} either adds or subtracts current from the input node, the current D_1 will adjust to satisfy $I_{D1} = I_{IN} + I_{REF1}$. Because I_{REF1} equals I_{REF2} and I_{D1} equals I_{D2} , a current equal to I_{IN} will flow in R_F . The output voltage is then $V_O = I_{IN}R_F$. The range of allowable I_{IN} is limited. Positive I_{IN} can be as large as I_{REF1} (10.5 μ A, min). At this point, D_1 supplies no current and the loop opens. Negative I_{IN} can be as large as that generated by D_1 with maximum LED output (recommended 10 μ A, max).

DC ERRORS

Errors in the ISO100 take the form of offset currents and voltages plus their drifts with temperature. These are shown in Figure 2.

A_1 and A_2 —assumed to be ideal amplifiers.

V_{OSO} and V_{OSI} —the input offset voltages of the output and input stage, respectively. V_{OSO} appears directly at the output, but, V_{OSI} appears at the output as

$$V_{OSI} \frac{R_F}{R_{IN}}, \quad (1)$$

see equation (2).

I_{OS} —the offset current. This is the current at the input necessary to make the output zero. It is equal to the combined effect of the difference between the bias currents of A_1 and A_2 and the matching errors in the optical components in the unipolar mode.

I_{REF1} and I_{REF2} —reference currents that, when connected to the inputs, enable bipolar operation. The two currents are trimmed, in the bipolar mode, to minimize the $I_{OS \text{ BIPOLAR}}$ error.

I_{D1} and I_{D2} —currents generated by each photodiode in response to the light from the LED.

A_e —gain error.

$$A_e = | \text{Ideal gain/Actual gain} | - 1$$

The output then becomes:

$$V_{OUT} = R_F \left[\left(\frac{V_{IN} \pm V_{OS}}{R_{IN}} - I_{REF1} \pm I_{OS} \right) (1 + A_e) + I_{REF2} \right] \pm V_{OSO} \quad (2)$$

The total input referred offset voltage of the ISO100 can be simplified in the unipolar case by assuming that $A_e = 0$ and $V_{IN} = 0$:

$$V_{OUT} \approx R_F \left[\frac{\pm V_{OSI}}{R_{IN}} \pm I_{OS \text{ UNIPOLAR}} \right] \pm V_{OSO} \quad (3)$$

This voltage is then referred back to the input by dividing by R_F/R_{IN} .

$$V_{OS (RTI)} = (\pm V_{OSI}) \pm R_{IN} (I_{OS \text{ UNIPOLAR}}) + V_{OSO} (R_F/R_{IN}) \quad (4)$$

Example 1. Refer to Figure 2 and Electrical Specifications Table.

Given: $I_{OS \text{ BIPOLAR}} = +35\text{nA}$
 $R_{IN} = 100\text{k}\Omega$
 $R_F = 1\text{M}\Omega$ (gain = 10)
 $V_{OSI} = +200\mu\text{V}$
 $V_{OSO} = +200\mu\text{V}$

Find: The total offset voltage error referred to the input and output when $V_{IN} = 0\text{V}$.

V_{OS} total RTI

$$= \{ [\pm V_{OSI} \pm R_{IN} (I_{OS \text{ BIPOLAR}}) - R_{IN} (I_{REF1})] [1 + A_e] + R_{IN} I_{REF2} \} \pm V_{OSO} (R_F/R_{IN})$$

$$= \{ [+200\mu\text{V} + 100\text{k}\Omega (35\text{nA}) - 100\text{k}\Omega (12.5\mu\text{A})] [1.02] + 100\text{k}\Omega (12.5\mu\text{A}) \} + 200\mu\text{V} / (1\text{M}\Omega / 100\text{k}\Omega)$$

$$= \{ [0.2\text{mV} + 3.5\text{mV} - 1.25\text{V}] [1.02] + 1.25\text{V} \} + 0.02\text{mV}$$

$$= -21.2\text{mV}$$

V_{OS} total RTO

$$= V_{OS} \text{ total RTI} \times R_F/R_{IN}$$

$$= -21.2\text{mV} \times 10$$

$$= -212\text{mV}$$

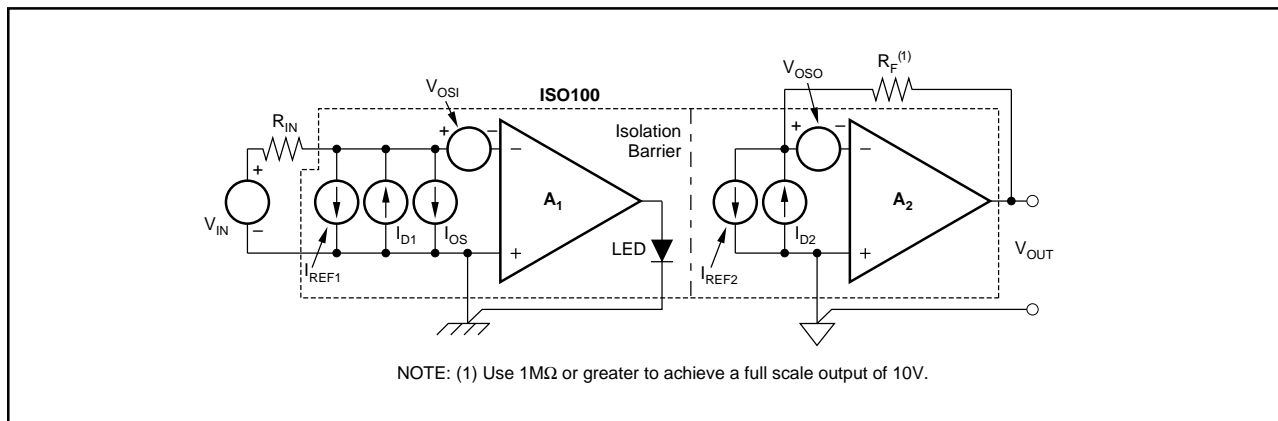


FIGURE 2. Circuit Model for DC Errors in the ISO100.

NOTE: This error is dominated by $I_{OS \text{ BIPOLAR}}$ and the reference current times the gain error (which appears as an offset). The error for unipolar operation is much lower. The error due to offset current can be zeroed using circuits shown in Figures 6 and 7. The gain error is adjusted by trimming either R_F or R_{IN} .

COMMON-MODE AND HIGH VOLTAGE ERRORS

Figure 3 shows a model of the ISO100 that can be used to analyze common-mode and high voltage behavior.

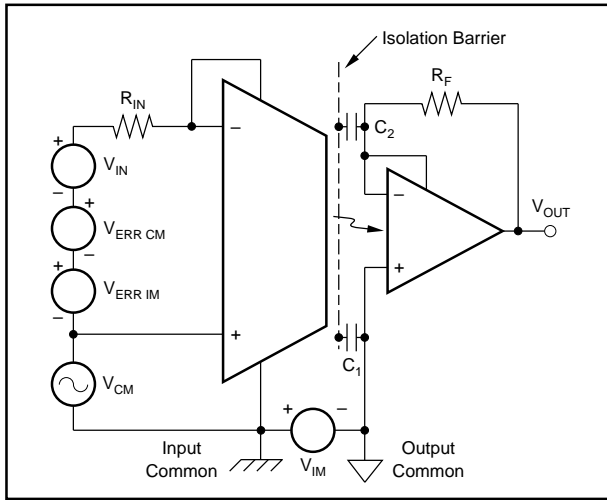


FIGURE 3. High Voltage Error Model.

Definitions of CMR and IMR

I_{OS} is defined as the input current required to make the ISO100's output zero. CMRR and IMRR in the ISO100 are expressed as conductances. CMRR defines the relationship between a change in the applied common-mode voltage (V_{CM}) and the change in I_{OS} required to maintain the amplifier's output at zero:

$$CMRR \text{ (I-mode)} = \Delta I_{OS} / \Delta V_{CM} \text{ in nA/V} \quad (5)$$

$$CMRR \text{ (V-mode)} = \left[\frac{\Delta I_{OS}}{\Delta V_{CM}} \right] R_{IN} = \frac{\Delta V_{ERR \text{ CM}}}{\Delta V_{CM}} \text{ in V/V} \quad (6)$$

IMRR defines the relationship between a change in the applied isolation mode voltage (V_{IM}) and the change in I_{OS} required to maintain the amplifier's output to zero:

$$IMRR \text{ (I-mode)} = \frac{\Delta I_{OS}}{\Delta V_{IM}} \text{ in pA/V} \quad (7)$$

$$IMRR \text{ (V-mode)} = \left[\frac{\Delta I_{OS}}{\Delta V_{IM}} \right] R_{IN} = \frac{\Delta V_{ERR \text{ IM}}}{\Delta V_{IM}} \text{ in V/V} \quad (8)$$

CMRR and IMRR in V/V are a function of R_{IN} .

V_{IM} is the voltage between input common and output common.

V_{CM} is the common-mode voltage (noise that is present on both input lines, typically 60Hz).

V_{ERR} is the equivalent error signal, applied in series with the input voltage, which produces an output error identical to that produced by application of V_{CM} and V_{IM} .

CMRR and IMRR are the common-mode and isolation-mode rejection ratios, respectively.

Total Capacitance (C_1 and C_2) is distributed along the isolation barrier. Most of the capacitance is coupled to low impedance or noncritical nodes and affects only the leakage current. Only a small capacitance (C_2) couples to the input of the second stage, and contributes to IMRR.

Example 2. Refer to Figure 3 and Electrical Specification Table.

Given: $V_{CM} = 1\text{VAC peak at } 60\text{Hz}$, $V_{IM} = 200\text{VDC}$,
 $CMRR = 3\text{nA/V}$, $IMRR = 5\text{pA/V}$,
 $R_{IN} = 100\text{k}\Omega$, $R_F = 1\text{M}\Omega$
 (Gain = 10)

Find: The error voltage referred to the input and output when $V_{IN} = 0\text{V}$

$$\begin{aligned} V_{ERR \text{ RTI}} &= (V_{CM})(CMRR)(R_{IN}) + (V_{IM})(IMRR)(R_{IN}) \\ &= 1\text{V} (3\text{nA/V})(100\text{k}\Omega) \\ &\quad + 200\text{V} (5\text{pA/V})(100\text{k}\Omega) \\ &= 0.3\text{mV} + 0.1\text{mV} \\ &= 0.4\text{mV} \end{aligned}$$

$$\begin{aligned} V_{ERR \text{ RTO}} &= V_{ERR \text{ RTI}} (R_F/R_{IN}) \\ &= 0.4\text{mV} (10) \\ &= 4\text{mV (with DC IMRR)} \end{aligned}$$

NOTE: This error is dominated by the CMRR term.

For purposes of comparing CMRR and IMRR directly with dB specifications, the following calculations can be performed:

$$\begin{aligned} CMRR \text{ in V/V} &= CMRR \text{ (I-mode)}(R_{IN}) \\ &= 3\text{nA/V} (100\text{k}\Omega) = 0.3\text{mV/V} \end{aligned}$$

$$CMR = 20 \text{ LOG } (0.3\text{mV/V}) = -70\text{dB at } 60\text{Hz}$$

$$\begin{aligned} IMRR \text{ in V/V} &= IMRR \text{ (I-mode)}(R_{IN}) = 5\text{pA/V}(100\text{k}\Omega) \\ &= 0.5\mu\text{V/V} \end{aligned}$$

$$IMR = 20 \text{ LOG } (0.5 \times 10^{-6}\text{V/V}) = -126\text{dB at DC}$$

Example 3.

In Example 3, V_{IM} is an AC signal at 60Hz and

$$IMRR = \frac{400\text{pA}}{V}$$

$$\begin{aligned} V_{ERR \text{ RTI}} &= V_{ERR \text{ CM}} + V_{ERR \text{ IM}} \\ &= 0.3\text{mV} + 200\text{V} (400\text{pA/V})(100\text{k}\Omega) \\ &= 8.3\text{mV} \end{aligned}$$

$$V_{ERR \text{ RTO}} = 83\text{mV (with AC IMRR)}$$



Example 4.

Given: Total error RTO from Examples 1 and 3 as 378mV worst case.

Find: Percent error of +10V full scale output

$$\begin{aligned} \% \text{ Error} &= \frac{V_{\text{ERR TOTAL}}}{V_{\text{FS}}} \times 100\% \\ &= \frac{378\text{mV}}{10\text{V}} \times 100\% \\ &= 3.78\% \end{aligned}$$

NOISE ERRORS

Noise errors in the unipolar mode are due primarily to the optical cavity. When the full 60kHz bandwidth is not needed, the output noise of the ISO100 can be limited by either a capacitor, C_F , in the feedback loop or by a low-pass filter following the output. This is shown in Figure 4. Noise in the bipolar mode is due primarily to the reference current sources, and can be reduced by the low-pass filters shown in Figure 5.

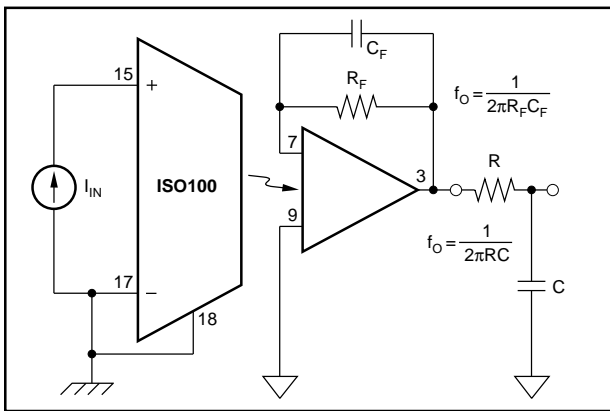


FIGURE 4. Two Circuit Techniques for Reducing Noise in the Unipolar Mode.

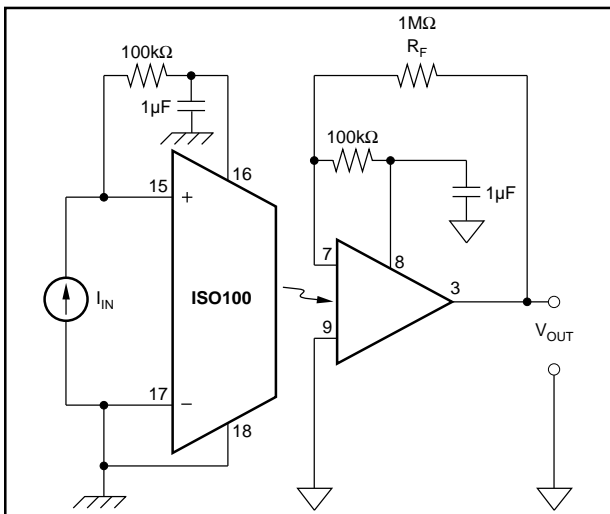


FIGURE 5. Circuit Techniques for Reducing Noise from the Current Sources in the Bipolar Mode.

OPTIONAL ADJUSTMENTS

There are two major sources of offset error: offset voltage and offset current. V_{OSI} and V_{OSO} of the input and output amplifiers can be adjusted independently using external potentiometers. An example is shown in Figure 17. Note that V_{OSO} (500μV, max) appears directly at the output, but V_{OSI} appears at the output multiplied by gain (R_F/R_{IN}). In general, V_{OS} is small compared to the effect of I_{OS} (see Example 1). To adjust for I_{OS} use a circuit which intentionally unbalances the offset in one direction and then allows for adjustment back to zero.

Figure 6 shows how to adjust unipolar errors at zero input. The unipolar amplifier can be used down to zero input if it is made to be "slightly bipolar." By sampling the reference current with R_5 and R_6 , the minimum current required to keep the input stage in the linear region of operation can be established. R_7 and R_8 are adjusted to cancel the offset created in the input stage. This brings the output to zero, when the input is zero. Although the amplifier can now operate down to zero input voltage, it has only a small portion of the current drain and noise that the true bipolar configuration would have.

Adjusting the bipolar errors is illustrated in Figure 7. Each of the errors are adjusted in turn. With V_{IN} = "open," I_{OS} is trimmed by adjusting R_{10} to make the output zero. R_G is then adjusted to trim the gain error. The effects of offset voltage are removed by adjusting R_{14} .

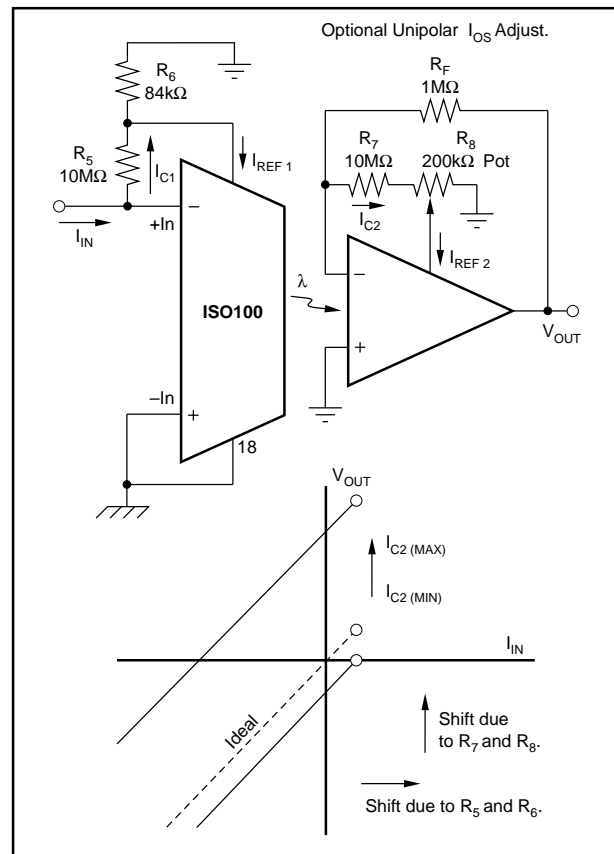


FIGURE 6. Adjusting the Unipolar Amplifier Errors at Zero Input.

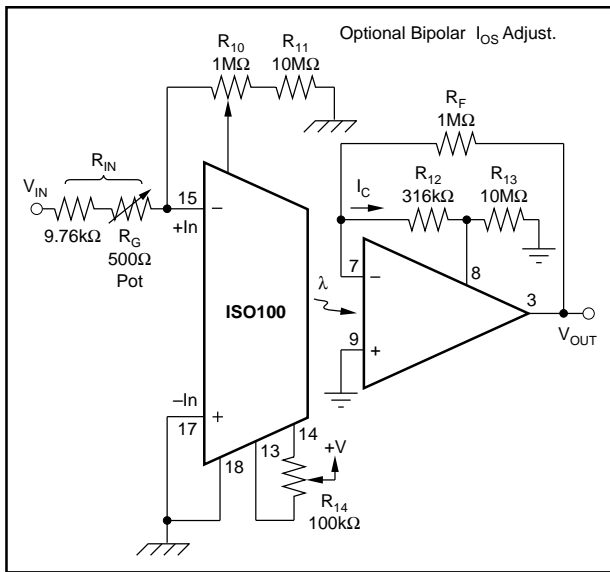


FIGURE 7. Adjusting the Bipolar Errors.

BASIC CIRCUIT CONNECTIONS

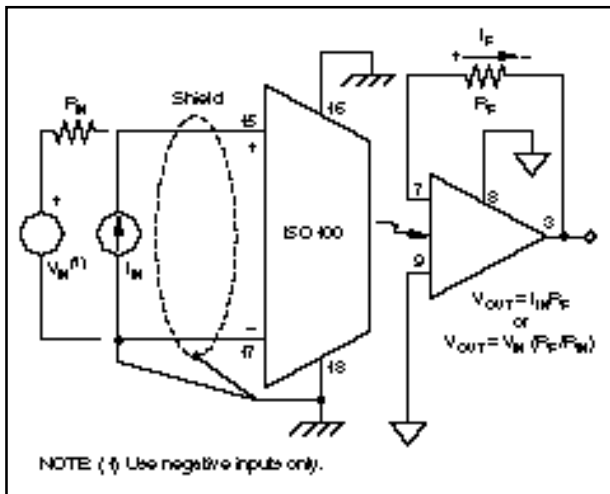


FIGURE 8. Unipolar Noninverting.

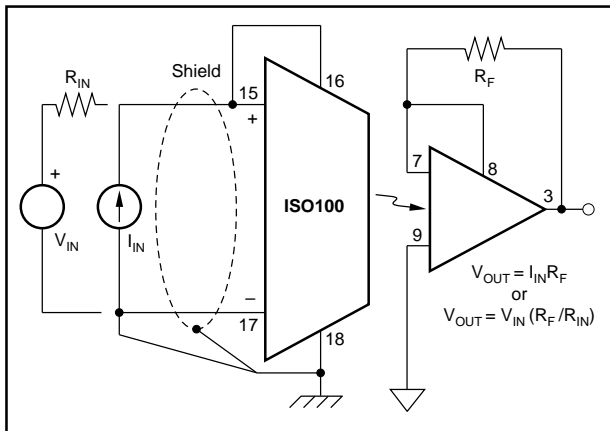


FIGURE 9. Bipolar Noninverting.

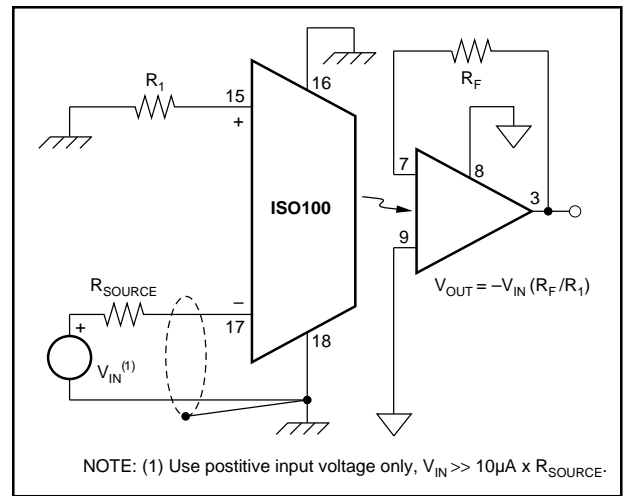


FIGURE 10. Unipolar Inverting.

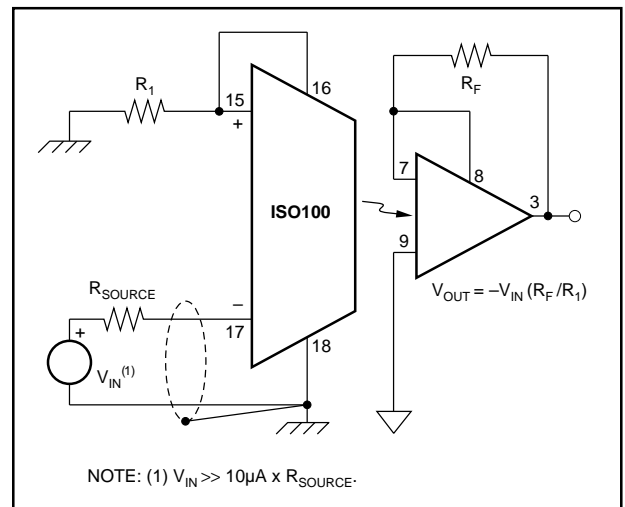


FIGURE 11. Bipolar Inverting.

APPLICATION INFORMATION

The small size, low offset and drift, wide bandwidth, ultra-low leakage, and low cost, make the ISO100 ideal for a variety of isolation applications. The basic mode of operation of the ISO100 will be determined by the type of signal and application.

Major points to consider when designing circuits with the ISO100.

1. Input Common (pin 18) and -In (pin 17) should be grounded through separate lines. The Input Common can carry a large DC current and may cause feedback to the signal input.
2. Use shielded or twisted pair cable at the input for long lines.
3. Care should be taken to minimize external capacitance across the isolation barrier.



4. The distance across the isolation barrier, between external components and conductor patterns, should be maximized to reduce leakage and arcing.
5. Although not an absolute requirement, the use of conformally-coated printed circuit boards is recommended.
6. When in the unipolar mode, the reference currents (pins 8 and 16) must be terminated. I_{IN} should be greater than 20nA to keep internal LED on.
7. The noise contribution of the reference currents will cause the bipolar mode to be noisier than the unipolar mode.
8. The maximum output voltage swing is determined by I_{IN} and R_F .

$$V_{SWING} = I_{IN\ MAX} \times R_F$$

9. A capacitor (about 3pF) can be connected across R_F to compensate for peaking in the frequency response. The peaking is caused by the pole generated by R_F and the capacitance at the input of the output amplifier.

Figure 12 through 18 show applications of the ISO100.

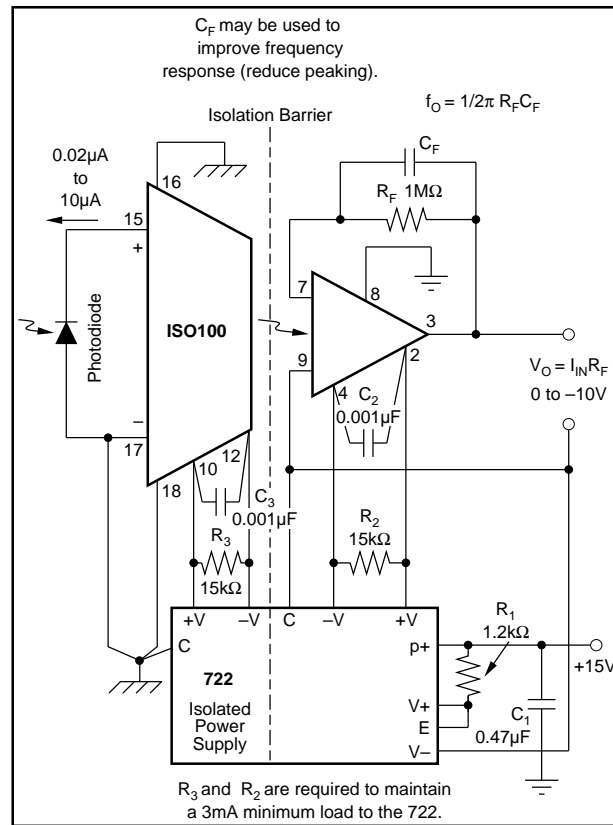


FIGURE 12. Two-Port Isolation Photodiode Amplifier Unipolar.

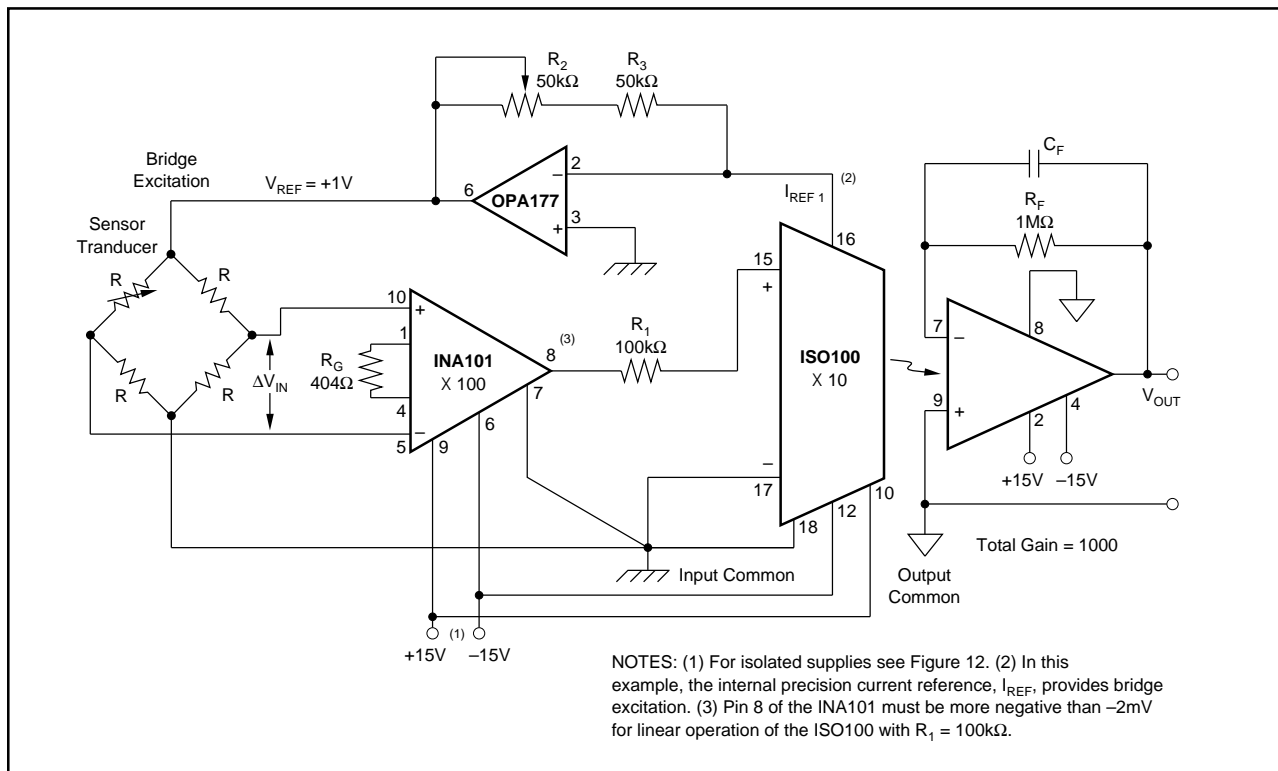


FIGURE 13. Precision Bridge Isolation Amplifier (Unipolar).

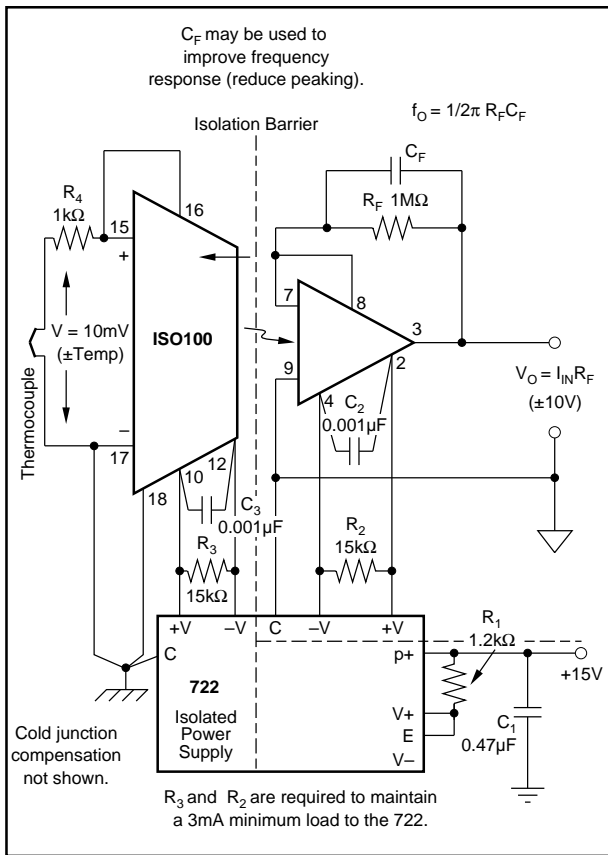


FIGURE 14. Three-Port Isolation Thermocouple Amplifier (Bipolar).

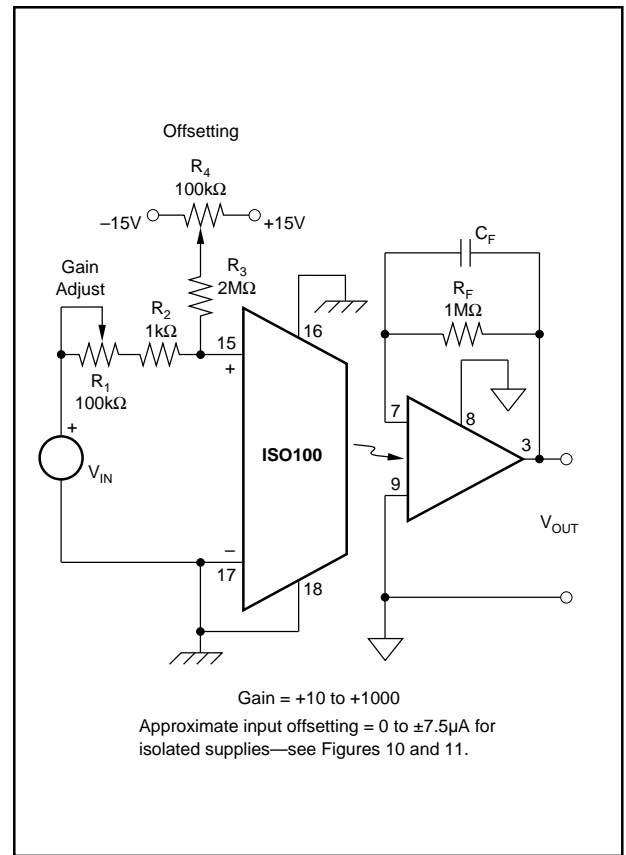


FIGURE 15. Isolated Test Equipment Amplifier (Unipolar with Offsetting).

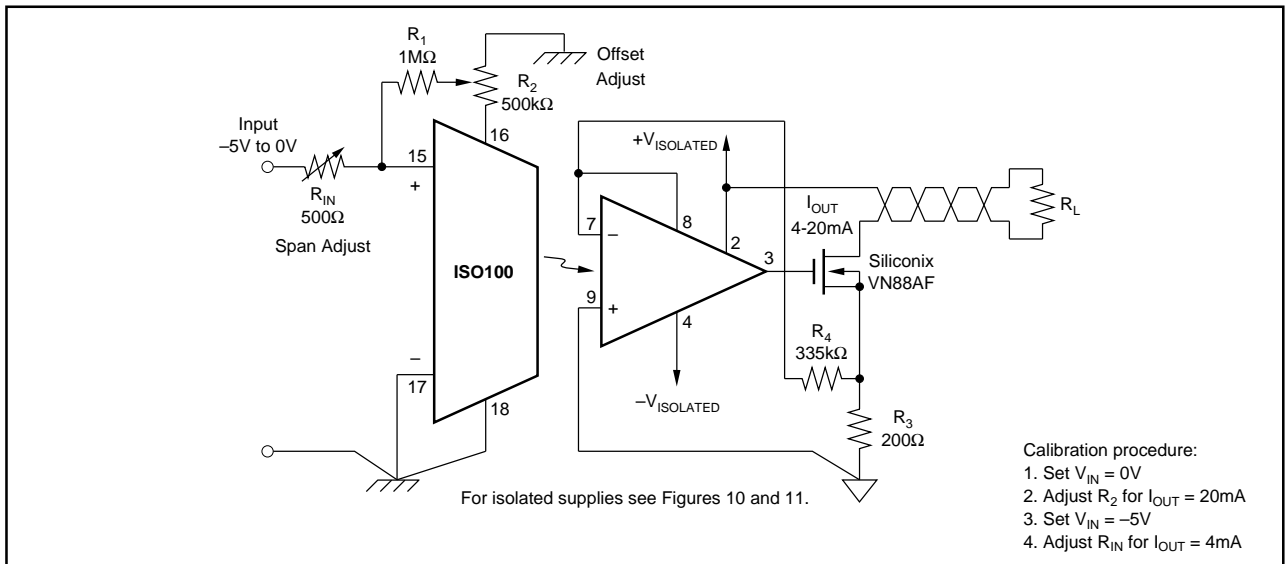


FIGURE 16. Isolated 4mA to 20mA Transmitter (Example of an isolated voltage controlled current source).



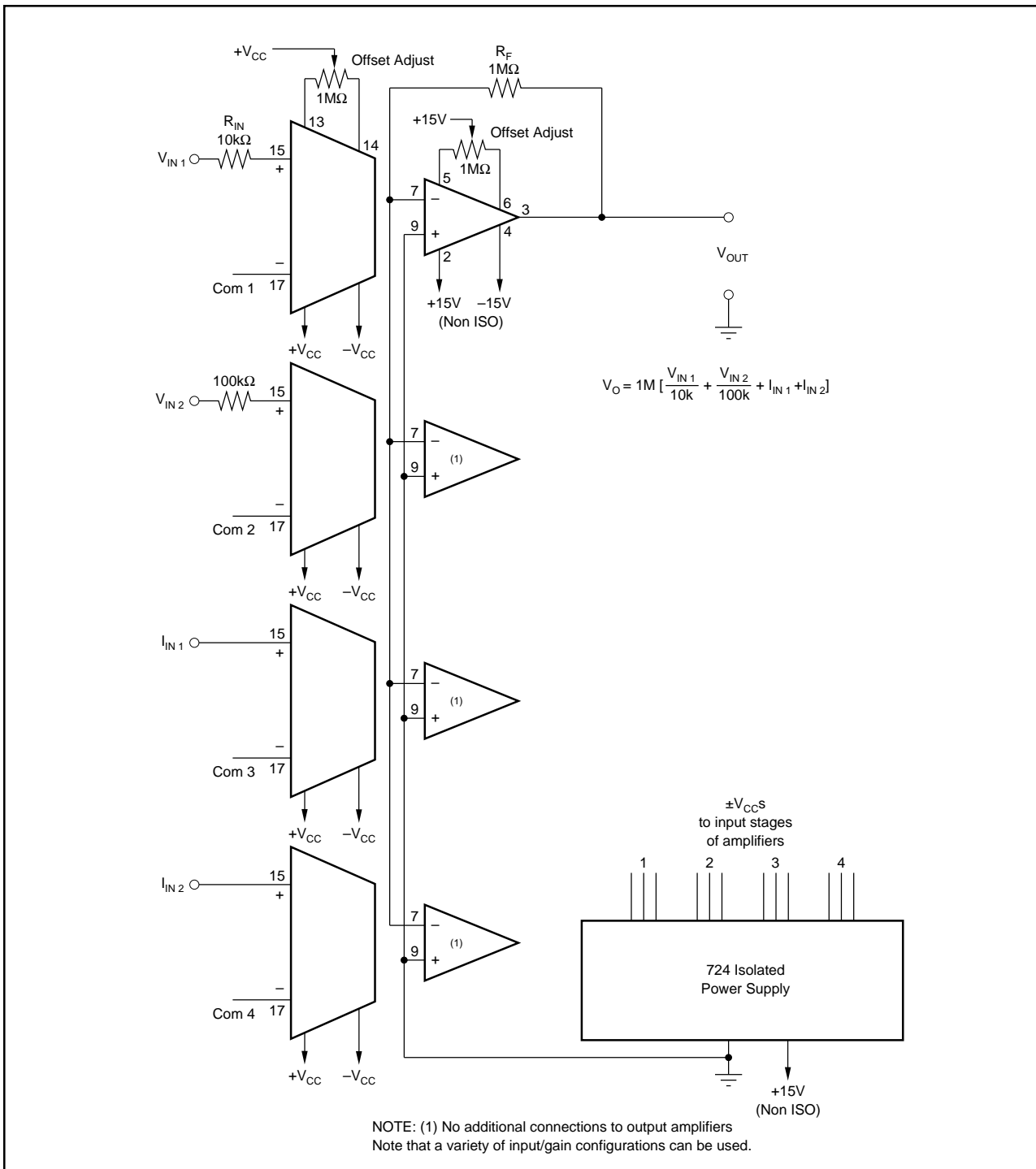


FIGURE 17. Four-Port Isolated Summing Amplifier (Unipolar).

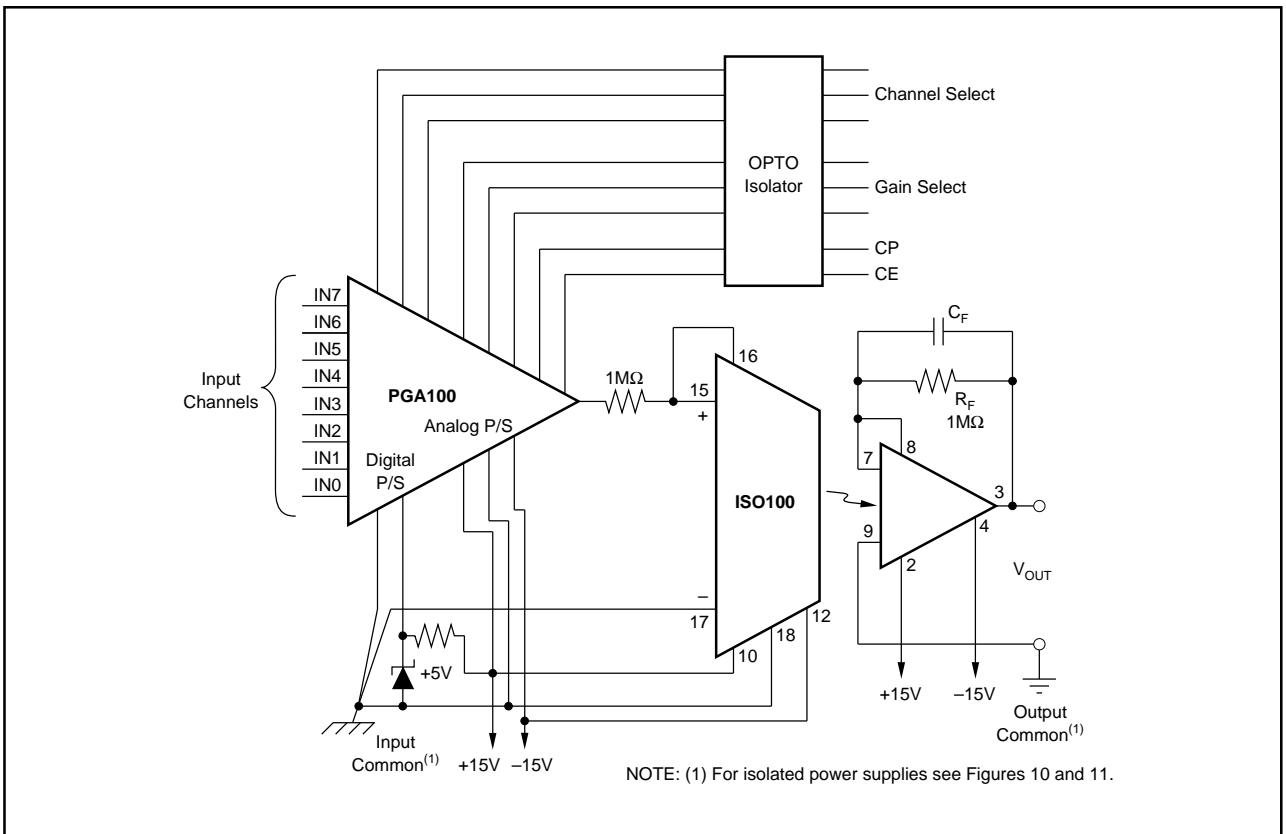


FIGURE 18. Multiple Channel Isolation Amplifier (Bipolar) with Programmable Gain (useful in data acquisition systems).

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